L Number	Hits		DB	Time stamp
1	1	6037712.pn.	USPAT;	2003/07/12 17:54
			US-PGPUB	
-	65	(TFT transistor) and ((insulat\$3 dielectric) same (SIN SION (silicon	USPAT;	2003/07/12 10:47
		near2 (nitride oxynitride)))) and ((organic near2 (element layer	US-PGPUB	
		film electroluminecen\$2 EL)) (light near2 (emitting emission		
		emitter))) and (partition rampart ridge rib barrier wall spacer) and		
	202	313/498-512.ccls.	LICDAT	2002/07/04 40.46
-	302	(TFT transistor) and (insulat\$3 dielectric) and ((organic near2	USPAT;	2003/07/01 10:46
		(element layer film electroluminecen\$2 EL)) (light near2 (emitting	US-PGPUB	
l		emission emitter))) and (partition rampart ridge rib barrier wall		
	2	spacer) and 313/495-512.ccls. ("4266223"   "5384517").PN.	USPAT	2003/06/30 16:29
	17	5640067,URPN.	USPAT	2003/06/30 16:29
	10	3040007.0KFN.   ("5247190"   "5306651"   "5399502"   "5594569"   "5640067"	USPAT	2003/06/30 16:39
	10	"5643826"   "5731613"   "5897328"   "5923962"   "6048758"	USPAT	2003/00/30 10.39
1		"2001/0004121").PN.		
_	2	6461899.URPN.	USPAT	2003/06/30 16:43
_	246	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2	USPAT;	2003/00/30 10:43
	210	(element layer film electroluminecen\$2 EL)) (light near2 (emitting	US-PGPUB	2005/07/01 11:00
		emission emitter))) and (partition rampart ridge rib barrier wall	03 ( 0, 0,	
		spacer) and 313/495-512.ccls.) not @ad>20011108		
_	1620	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2	USPAT;	2003/07/01 11:03
	1020	(element layer film electroluminecen\$2 EL)) (light near2 (emitting	US-PGPUB	2005,07,01 11105
		emission emitter))) and (partition rampart ridge rib barrier wall	00,0.00	
		spacer) and 257/\$.ccls.) not @ad>20001110		
-	5408	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2	USPAT;	2003/07/01 11:16
		(element layer film electroluminecen\$2 EL)) (light near2 (emitting	US-PGPUB	
		emission emitter))) and (partition rampart ridge rib barrier wall		
		spacer)) not @ad>20001110		
-	73816	257/\$4.ccls.	USPAT;	2003/07/01 11:06
			US-PGPUB	
- {	999	(((TFT transistor) and (insulat\$3 dielectric) and ((organic near2	USPAT;	2003/07/01 11:06
		(element layer film electroluminecen\$2 EL)) (light near2 (emitting	US-PGPUB	
İ		emission emitter))) and (partition rampart ridge rib barrier wall		
		spacer)) not @ad>20001110) and 257/\$4.ccls.		
-	927	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2	USPAT;	2003/07/01 12:38
		((light near2 (emitting emission emitter)) electroluminecen\$2 EL))	US-PGPUB	
		(light near3 (layer element film) near2 (emitting emission		
		emitter))) and (partition rampart ridge rib barrier wall spacer)) not		
	77701	@ad>20001110	LICDAT.	2002/07/04 44.50
•	77791	313/495-512.ccls. 257/\$3.ccls.	USPAT;	2003/07/01 11:56
_	361	(((TFT transistor) and (insulat\$3 dielectric) and ((organic near2	US-PGPUB USPAT;	2003/07/01 11:56
-	301	(((Iight near2 (emitting emission emitter)) electroluminecen\$2 EL))	US-PGPUB	2003/07/01 11.30
		(light near3 (layer element film) near2 (emitting emission	US-FGFUB	
		emitter))) and (partition rampart ridge rib barrier wall spacer)) not		
		@ad>20001110) and (313/495-512.ccls. 257/\$3.ccls.)		}
_	8	((TFT transistor) and (insulat\$3 dielectric) and ((organic near2	EPO; JPO;	2003/07/01 12:41
	· ·	((light near2 (emitting emission emitter)) electroluminecen\$2 EL))	DERWENT	2005/07/01 12:11
		(light near3 (layer element film) near2 (emitting emission		
ŀ		emitter))) and (partition rampart ridge rib barrier wall spacer)) not		
		@pd>20001110		
-	22	((TFT transistor) same (insulat\$3 insolat\$3 isolat\$3 dielectric)) and	EPO; JPO;	2003/07/03 16:02
		((EL electroluminescen\$2 (light near2 (emitting emission	DERWENT	
		emitter))) near3 (device display panel element)) and (partition		
		barrier rib spacer rampart wall)		• .
-	685	((TFT transistor) same (insulat\$3 insolat\$3 isolat\$3 dielectric)) and	USPAT;	2003/07/03 17:15
		((EL electroluminescen\$2 (light near2 (emitting emission	US-PGPUB	
		emitter))) near3 (device display panel element)) and (partition		
		barrier rib spacer rampart wall) and (313/495-512.ccls.		
		257/\$3.ccls.)	[	

-	369	(((TFT transistor) same (insulat\$3 insolat\$3 isolat\$3 dielectric))	USPAT;	2003/07/03 16:46
		and ((EL electroluminescen\$2 (light near2 (emitting emission	US-PGPUB	
		emitter))) near3 (device display panel element)) and (partition		
		barrier rib spacer rampart wall) and (313/495-512.ccls.		
		257/\$3.ccls.)) not @ad>20001110		
-	24	("4774556"   "4780424"   "4861730"   "4929988"   "5017977"	USPAT	2003/07/03 16:36
		"5021848"   "5053842"   "5071782"   "5078498"   "5146426"		
		"5202576"   "5323042"   "5350937"   "5594569"   "5633519"		,
		"5643826"   "5923962"   "5939731"   "5965915"   "6055034"		
		"6166414"   "6172671"   "6198133"   "6281552").PN.		
-	2133	semiconductor adj energy adj laboratory\$.as.	USPAT;	2003/07/03 16:45
			US-PGPUB	
-	211	(((TFT transistor) same (insulat\$3 insolat\$3 isolat\$3 dielectric))	USPAT;	2003/07/03 16:47
		and ((EL electroluminescen\$2 (light near2 (emitting emission	US-PGPUB	
		emitter))) near3 (device display panel element)) and (partition		
		barrier rib spacer rampart wall) and (313/495-512.ccls.		
		257/\$3.ccls.)) not @pd>20001110		
-	2	("5742129"   "5804917").PN.	USPAT	2003/07/03 17:16
-	2	("5631664"   "5684365").PN.	USPAT	2003/07/03 17:17
-	59	5684365.URPN.	USPAT	2003/07/03 17:17
-	1118	313/504.ccls.	USPAT;	2003/07/03 17:18
			US-PGPUB	
-	6	("4015166"   "5550066"   "5684365"   "5742129"   "6072450"	USPAT	2003/07/03 17:19
		"6091382").PN.		
-	204	313/504.ccls. and transistor	USPAT;	2003/07/07 10:37
	_		US-PGPUB	
-	5	("4734623"   "5518808"   "5565742"   "5859508"	USPAT	2003/07/07 10:34
	_	"5936347").PN.		
-	3	("5352543"   "5371434"   "5384517").PN.	USPAT	2003/07/07 10:35
-	1	"5156924".PN.	USPAT	2003/07/07 10:36
-	11	5352543.URPN.	USPAT	2003/07/07 10:36
-	478	313/498-512.ccls. and transistor	USPAT;	2003/07/07 10:37
	122	212/F04 cdc and TFT	US-PGPUB	2002/07/07 10:42
-	122	313/504.ccls. and TFT	USPAT;	2003/07/07 10:42
_	4	("5004950"   "5194290"   "5523770"   "5804917").PN.	US-PGPUB USPAT	2003/07/07 10:41
-	581	313/504.ccls. and (carbon diamond graphite)	USPAT;	2003/07/07 10:41
-	201	515/504.ccis. and (carbon diamond graphite)	US-PGPUB	2003/07/07 10:42
_	280	313/504.ccls. and ((carbon diamond graphite) with (dielectric	USPAT;	2003/07/07 10:48
-	200	insulat\$3 layer film coat\$3))	US-PGPUB	2003/07/07 10.46
_	4	("5004950"   "5194290"   "5523770"   "5804917").PN.	USPAT	2003/07/07 10:46
_	3	6114183.URPN.	USPAT	2003/07/07 10:46
_	445	345/92.ccls.	USPAT;	2003/07/07 10:48
	1.13	3 13/ 52.0013.	US-PGPUB	2003/07/07 10.40
-	65	345/92.ccls. and (((organic near3 (EL electroluminescen\$2)) (light	USPAT;	2003/07/07 11:00
		near2 (emitting emission emitter))) near3 (element device display	US-PGPUB	2003/07/07 11:00
		panel))	00 1 01 05	
-	366	345/76-81.ccls. and (((organic near3 (EL electroluminescen\$2))	USPAT;	2003/07/07 11:04
		(light near2 (emitting emission emitter))) near3 (element device	US-PGPUB	2005/07/07 11:01
		display panel))	33 . 3. 35	
_	79	345/76-81.ccls. and (((organic near3 (EL electroluminescen\$2))	USPAT;	2003/07/07 11:05
		(light near2 (emitting emission emitter))) near3 (element device	US-PGPUB	=====
		display panel)) and (rampart barrier rib spacer partition ridge)		
-	340	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2	USPAT;	2003/07/12 13:24
		(nitride oxynitride))) and (transistor TFT thin-film-transistor) and	US-PGPUB	
		((EL electroluminescen\$2 (light near2 (emitting emission emissive		
		emitter))) near2 (element layer film)) and 313/500-512.ccls.		
-	1010	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2	USPAT;	2003/07/12 11:39
		(nitride oxynitride))) and (transistor TFT thin-film-transistor) and	US-PGPUB	
		((EL electroluminescen\$2 (light near2 (emitting emission emissive		
		emitter))) near2 (element layer film)) and 257/\$.ccls.		

-	784	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and	USPAT; US-PGPUB	2003/07/12 11:42
		((EL electroluminescen\$2 (light near2 (emitting emission emissive emitter))) near2 (element layer film)) and 257/\$3.ccls.		
-	481	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and	USPAT; US-PGPUB	2003/07/12 11:43
		((EL electroluminescen\$2 (light near2 (emitting emission emissive	0510100	
		emitter))) near2 (element layer film)) and (organic OLED) and 257/\$3.ccls.		
-	228	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and	USPAT; US-PGPUB	2003/07/12 12:04
		((EL electroluminescen\$2 (light near2 (emitting emission emissive	00 ( 0.00	
		emitter))) near2 (OLED organic) near2 (element layer film)) and 257/\$3.ccls.		
-	3	("5294870"   "5552547"   "5641611").PN.	USPAT	2003/07/12 11:51
-	172	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and	USPAT; US-PGPUB	2003/07/12 12:06
		((EL electroluminescen\$2 (light near2 (emitting emission emissive	U3-FGFUB	
		emitter))) near2 (OLED organic) near2 (element layer film)) and 345/\$3.ccls.		
-	0	(insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2	USPAT;	2003/07/12 12:06
		(nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive	US-PGPUB	
		emitter))) near2 (OLED organic) near2 (element layer film)) and		
_	134	169.3/\$3.ccls.   (insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2	USPAT;	2003/07/12 12:07
	154	(nitride oxynitride))) and (transistor TFT thin-film-transistor) and	US-PGPUB	2003/07/12 12:07
		((EL electroluminescen\$2 (light near2 (emitting emission emissive		
		emitter))) near2 (OLED organic) near2 (element layer film)) and 438/\$3.ccls.		
-	162	((insulat\$3 dielectric SIN SION "Si.sub.3 N.sub.4" (silicon near2	USPAT;	2003/07/12 12:07
		(nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2 (emitting emission emissive	US-PGPUB	
		emitter))) near2 (OLED organic) near2 (element layer film)) and		
		345/\$3.ccls.) not ((insulat\$3 dielectric SIN SION "Si.sub.3		
		N.sub.4" (silicon near2 (nitride oxynitride))) and (transistor TFT thin-film-transistor) and ((EL electroluminescen\$2 (light near2		
		(emitting emission emissive emitter))) near2 (OLED organic) near2		
-	784	(element layer film)) and 257/\$3.ccls.) (DLC diamond-like (diamond near2 like) carbon) and ((EL	USPAT;	2003/07/12 13:26
		electroluminescen\$2 (light near2 (emitting emission emissive	US-PGPUB	2005/07/12 15:20
_	520	emitter))) near2 (element layer film)) and 313/500-512.ccls. (DLC diamond-like (diamond near2 like) carbon) and ((EL	USPAT;	2002/07/12 12:26
	320	electroluminescen\$2 (light near2 (emitting emission emissive	US-PGPUB	2003/07/12 13:26
		emitter))) near2 (organic OLED) near2 (element layer film)) and		
_	1	313/500-512.ccls. 5952708.pn.	USPAT;	2003/07/12 13:39
		·	US-PGPUB	
-	62	((insulat\$3 dielectric) same (DLC diamond-like carbide (diamond near2 like) carbon)) and ((EL electroluminescen\$2 (light near2	USPAT; US-PGPUB	2003/07/12 14:05
		(emitting emission emissive emitter))) near2 (organic OLED) near2	U3-FUFUD	
	70	(element layer film)) and 313/500-512.ccls.	LICOAT	2002/07/12 11 55
-	70	((protect\$3) same (DLC diamond-like carbide (diamond near2 like) carbon)) and ((EL electroluminescen\$2 (light near2 (emitting	USPAT; US-PGPUB	2003/07/12 14:30
		emission emissive emitter))) near2 (organic OLED) near2 (element	35 / 3/ 05	
_	9	layer film)) and 313/500-512.ccls.   ("5276380"   "5294869"   "5521465"   "5587589"   "5652067"	LICDAT	2002/07/12 14:11
	7	( 3276360   3294669   3321463   3387389   3632067"     "5656508"   "5693962"   "5701055"   "5773931").PN.	USPAT	2003/07/12 14:11
-	1	6037712.pn.	USPAT;	2003/07/12 17:54
	L		US-PGPUB	<u> </u>